L Number	Hits	Search Text	DB	Time stamp
-	1	("20040124460").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:28
-	1130	(438/148,768,769,775,776,791,792,793,794).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:43
-	2141	(nitriding nitridation) with (poly polysilicon gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:05
-	147	((438/148,768,769,775,776,791,792,793,794).CCLS.) and ((nitriding nitridation) with (poly polysilicon gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:42
-	832	(nitriding nitridation) with (poly polysilicon gate near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:39
-	53	(((438/148,768,769,775,776,791,792,793,794).CCLS.) and ((nitriding nitridation) with (poly polysilicon gate electrode))) and ((nitriding nitridation) with (poly polysilicon gate near electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 10:39
-	264	(rtn) with (poly polysilicon gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:44
-	12	((438/148,768,769,775,776,791,792,793,794).CCLS.) and ((rtn) with (poly polysilicon gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:45
-	679	(rn) with (poly polysilicon gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:45
-	0	((438/148,768,769,775,776,791,792,793,794).CCLS.) and ((rn) with (poly polysilicon gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:45
-	80	(rpn) with (poly polysilicon gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:45
-	11	((438/148,768,769,775,776,791,792,793,794).CCLS.) and ((rpn) with (poly polysilicon gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:47

-	1810	(oxidation oxide oxidize) near2 side near2 (gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:48
-	2841	(nitriding nitridation rtp rtn) with (poly polysilicon gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 09:48
-	63	((oxidation oxide oxidize) near2 side near2 (gate electrode)) and ((nitriding nitridation rtp rtn) with (poly polysilicon gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 11:48
-	57	(nitriding nitridation) with (poly polysilicon gate electrode) and (metal titanium tungsten molybdium nickel cobalt) near nitride same (nitrided silicion near nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:35
-	21	("5147820" | "5256455" | "5279985" | "5352623" | "5438012" | "5486488" | "5508221" | "5619051" | "5696017" | "5763315" | "5801079" | "5805494" | "5807760" | "5811336" | "5854114" | "5856009" | "5858873" | "6146959" | "6171970" | "6277681" | "6319856").PN.	USPAT	2004/07/08 13:29
-	4436	((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly polysilicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:40
-	12068	((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:41
-	9288	(pattern patterning etch$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:43
-	3068	(pattern patterning etch$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si) and (((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:45
-	1130	(438/148,768,769,775,776,791,792,793,794).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:43

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-	63	((pattern patterning etch$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si) and (((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate electrode))) and ((438/148,768,769,775,776,791,792,793,794).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:46
-	665	(pattern patterning etch$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si) with (metal titanium tungsten molybdium nickel cobalt Ti W Mo Ni Co) and (((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 13:46
-	17	((pattern patterning etch$5) with (gate electrode) with (nitride nitrided nitridation) with (silicon poly polysilicon si) with (metal titanium tungsten molybdium nickel cobalt Ti W Mo Ni Co) and (((nitriding nitridation) with (thermal decoupled near plasma remote near plasma) dpn rpn cvd chemical near vapor near deposition ald atomic near layer near deposition) with (poly si polysilicon silicon gate electrode) with (silicon near nitride sin "si.sub.3n.sub.4" "si.sub.3 n.sub.4") and (poly si polysilicon silicon) with (gate electrode))) and ((438/148,768,769,775,776,791,792,793,794).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 15:36
-	25	surface near density near (nitrogen "n.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 17:24
-	3	("5719410").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 16:20
-	2	jp-60195975-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 17:25
-	990340	ITO, TAKASHI HORIE, HIROSHI SUGII, TOSHIHIRO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 17:26
-	990340	ITO, TAKASHI HORIE, HIROSHI SUGII, TOSHIHIRO TAKASHI-ITO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 17:26
-	3132	SUGII-TOSHIHIRO TAKASHI-ITO HORIE-HIROSHI ito-takashi TOSHIHIRO-SUGII	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/08 17:28

-	241	(438/$6 257/$6) and (SUGII-TOSHIHIRO TAKASHI-ITO HORIE-HIROSHI ito-takashi TOSHIHIRO-SUGII)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 09:47
-	33	4935804.URPN.	USPAT	2004/07/08 17:46
-	6	("3755026" | "4117506" | "4141022" | "4377857" | "4460980" | "4558344").PN.	USPAT	2004/07/08 17:46
-	73	(decoupled near plasma near nitridation remote near plasma near nitridation) with (poly polysilicon gate electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 09:48
-	0	(decoupled near plasma near nitridation remote near plasma near nitridation) with (poly polysilicon gate electrode) with (ammonia "nh.sub.3" "n h.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 09:49
-	2	(decoupled near plasma near nitridation remote near plasma near nitridation) with (poly polysilicon gate electrode) same (ammonia "nh.sub.3" "n h.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 09:53
-	6	(decoupled near plasma near nitridation dpn remote near plasma near nitridation rpn) with (poly polysilicon gate electrode) same (ammonia "nh.sub.3" "n h.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 09:56
-	4	((decoupled near plasma near nitridation dpn remote near plasma near nitridation rpn) with (poly polysilicon gate electrode) same (ammonia "nh.sub.3" "n h.sub.3")) not ((decoupled near plasma near nitridation remote near plasma near nitridation) with (poly polysilicon gate electrode) same (ammonia "nh.sub.3" "n h.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 09:53
-	8	(decoupled near plasma near nitridation dpn remote near plasma near nitridation rpn) with (poly polysilicon silicon si gate electrode) same (ammonia "nh.sub.3" "n h.sub.3") not ((decoupled near plasma near nitridation dpn remote near plasma near nitridation rpn) with (poly polysilicon gate electrode) same (ammonia "nh.sub.3" "n h.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 10:16
-	0	(decoupled near plasma near nitridation dpn remote near plasma near nitridation rpn) with (poly polysilicon silicon si gate electrode) same (ammonia "nh.sub.3" "n h.sub.3") with ("1000") near (w watt watts)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 10:16
-	1	(decoupled near plasma near nitridation dpn remote near plasma near nitridation rpn) with (poly polysilicon silicon si gate electrode) same (ammonia "nh.sub.3" "n h.sub.3") same ("1000") near (w watt watts)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 10:34
-	0	jp-200049159-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 10:34
-	2	jp-2000049159-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 10:34